



STD5NE10L

N - CHANNEL 100V - 0.3 Ω - 5A - DPAK/IPAK STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD5NE10L	100 V	< 0.4 Ω	5 A

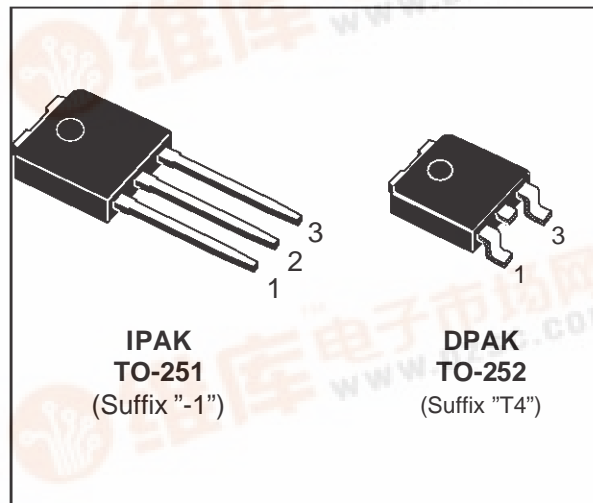
- TYPICAL R_{DS(on)} = 0.3 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- AVALANCHE RUGGED TECHNOLOGY
- 100 % AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- FOR TAPE & REEL AND OTHER PACKAGING OPTIONS CONTACT SALES OFFICES

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

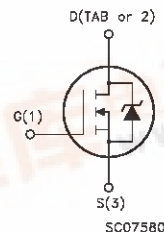
- DC MOTOR CONTROL (DISK DRIVES, etc.)
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION



**IPAK
TO-251**
(Suffix "-1")

**DPAK
TO-252**
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	100	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	5	A
I _D	Drain Current (continuous) at T _c = 100 °C	3.5	A
I _{DM} (●)	Drain Current (pulsed)	20	A
P _{tot}	Total Dissipation at T _c = 25 °C	25	W
	Derating Factor	0.2	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	6	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}



STD5NE10L

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	5	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	100	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	1.5	$^{\circ}C/W$
T_I	Maximum Lead Temperature For Soldering Purpose		275	$^{\circ}C$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	5	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 30 V$)	20	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	100			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 100^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10 V$ $I_D = 2.5 A$ $V_{GS} = 5 V$ $I_D = 2.5 A$		0.3 0.35	0.4 0.45	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$		5		A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 2.5 A$	2			S
C_{iss}	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		345	450	pF
C_{oss}	Output Capacitance			45	60	pF
C_{rss}	Reverse Transfer Capacitance			20	25	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 50\text{ V}$		7	9	ns
t_r	Rise Time	$I_D = 2.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		17	22	ns
Q_g	Total Gate Charge	$V_{DD} = 80\text{ V}$ $I_D = 5\text{ A}$ $V_{GS} = 5\text{ V}$		10	14	nC
Q_{gs}	Gate-Source Charge			5		nC
Q_{gd}	Gate-Drain Charge			4		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 80\text{ V}$		8	10	ns
t_f	Fall Time	$I_D = 5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		9	12	ns
t_c	Cross-over Time			19	25	ns

SOURCE DRAIN DIODE

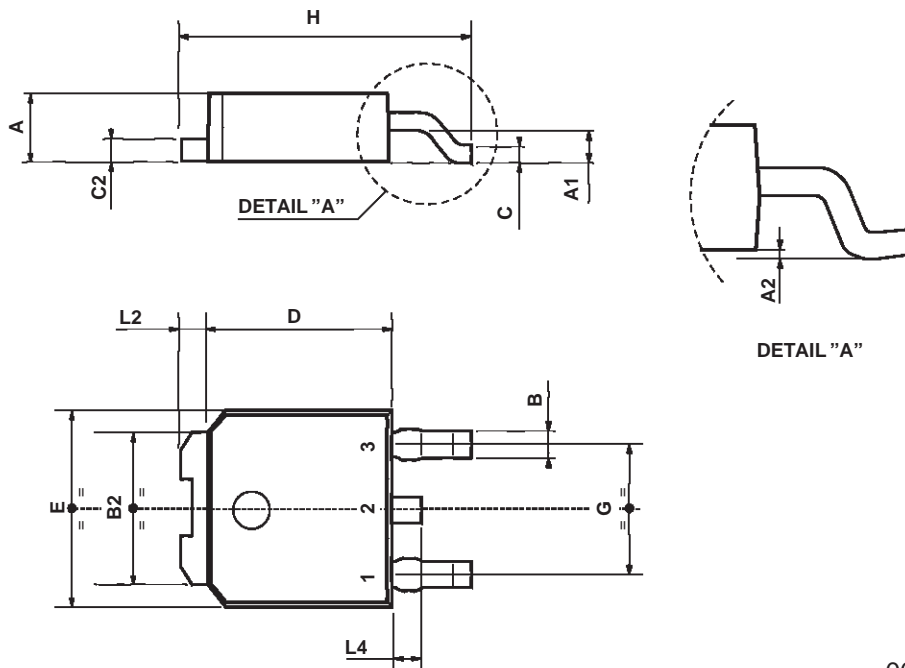
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				20	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 8\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 5\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		75		ns
Q_{rr}	Reverse Recovery Charge			190		μC
I_{RRM}	Reverse Recovery Current			5		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

TO-252 (DPAK) MECHANICAL DATA

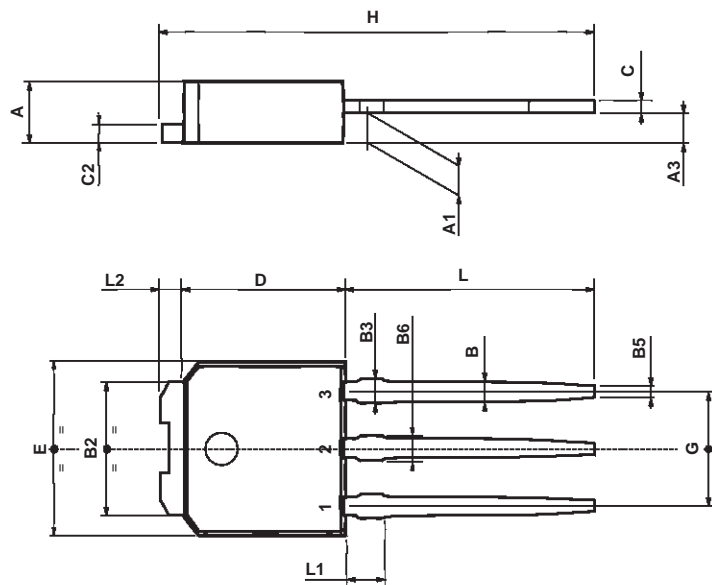
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



0068771-E

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